

isc Silicon PNP Darlington Power Transistor

TIP145T

DESCRIPTION

- High DC Current Gain-
: $h_{FE} = 1000(\text{Min}) @ I_C = -5\text{A}$
- Collector-Emitter Sustaining Voltage-
: $V_{CEO(\text{SUS})} = -60\text{V}(\text{Min})$
- Complement to Type TIP140T
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

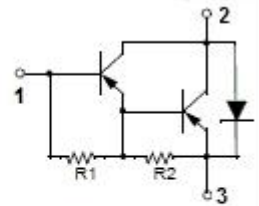
- Designed for general purpose amplifier and low frequency switching applications.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

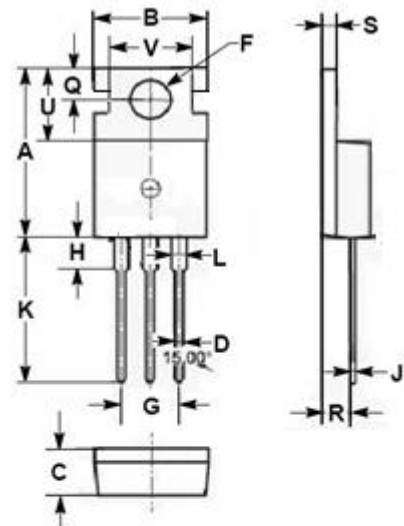
SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-10	A
I_{CM}	Collector Current-Peak	-15	A
I_B	Base Current- Continuous	-0.5	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	80	W
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.56	$^\circ\text{C/W}$



PIN 1. BASE
2. COLLECTOR
3. EMITTER
TO-220C package



DIM	mm	
	MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C = -30\text{mA}$, $I_B = 0$	-60			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C = -5\text{A}$, $I_B = -10\text{mA}$			-2.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C = -10\text{A}$, $I_B = -40\text{mA}$			-3.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -10\text{A}$, $I_B = -40\text{mA}$			-3.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -10\text{A}$; $V_{CE} = -4\text{V}$			-3.0	V
I_{CBO}	Collector Cutoff current	$V_{CB} = -60\text{V}$, $I_E = 0$			-1	mA
I_{CEO}	Collector Cutoff current	$V_{CE} = -30\text{V}$, $I_B = 0$			-2	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5\text{V}$; $I_C = 0$			-2	mA
h_{FE-1}	DC Current Gain	$I_C = -5\text{A}$; $V_{CE} = -4\text{V}$	1000			
h_{FE-2}	DC Current Gain	$I_C = -10\text{A}$; $V_{CE} = -4\text{V}$	500			

Switching Times

t_d	Delay Time	$V_{CC} = -30\text{V}$, $I_C = -5.0\text{A}$, $I_{B1} = -I_{B2} = -20\text{mA}$; $t_p = 20\mu\text{s}$ Duty Cycle $\leq 20\%$		0.15		μs
t_r	Rise Time			0.55		μs
t_{stg}	Storage Time			2.5		μs
t_f	Fall Time			2.5		μs

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TIP145T**NOTICE:**

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